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(54) **Title:** NEW SUSCEPTOR DESIGN TO REDUCE EDGE THERMAL PEAK

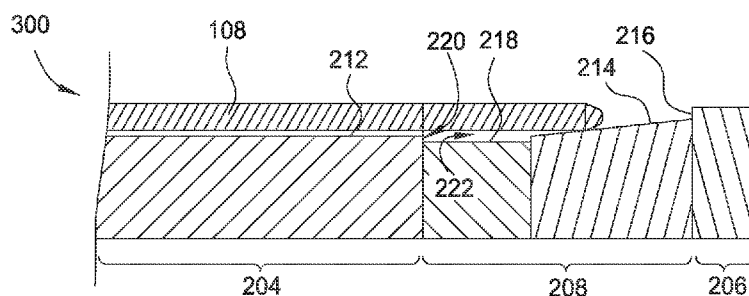


FIG. 3A

(57) **Abstract:** Implementations of the present disclosure generally relate to a susceptor for thermal processing of semiconductor substrates. In one implementation, the susceptor includes a first rim surrounding and coupled to an inner region, and a second rim disposed between the inner rim and the first rim. The second rim includes an angled support surface having a plurality of cut-outs formed therein, and the angled support surface is inclined with respect to a top surface of the inner region.